

<b>SANYO</b>	No.1070C	<b>2SC3151</b> NPN Triple Diffused Planar Silicon Transistor FOR SWITCHING REGULATOR
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**Features**

- . High breakdown voltage ( $V_{CBO} \geq 900V$ )
- . High switching speed
- . Wide ASO

**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

			unit
Collector-to-Base Voltage	$V_{CBO}$	900	V
Collector-to-Emitter Voltage	$V_{CEO}$	800	V
Emitter-to-Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	1.5	A
Peak Collector Current	$i_{cp}$	5	A
		PW $\leq 300\mu s$ , Duty Cycle $\leq 10\%$	
Base Current	$I_B$	0.8	A
Collector Dissipation	$P_C$	60	W
		$T_C = 25^\circ C$	
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

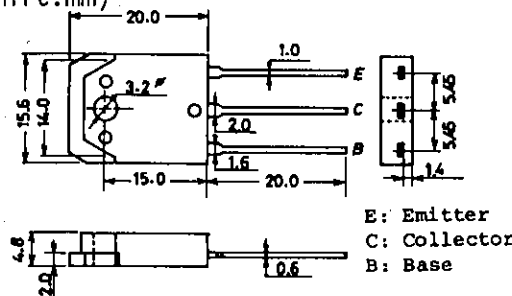
**Electrical Characteristics at  $T_a = 25^\circ C$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 800V, I_E = 0$			10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$			10	$\mu A$
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5V, I_C = 0.1A$	10*		40*	
	$h_{FE}(2)$	$V_{CE} = 5V, I_C = 0.5A$	8			
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 0.1A$		15		MHz
Output Capacitance	$c_{ob}$	$V_{CB} = 10V, f = 1MHz$		30		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 0.75A, I_B = 0.15A$			2.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 0.75A, I_B = 0.15A$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1mA, I_E = 0$	900			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 5mA, R_{BE} = \infty$	800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1mA, I_C = 0$	7			V
C-E Sustain Voltage	$V_{CEO(sus)}$	$I_C = 1.5A, L = 1mH, I_B = 0.5A$	800			V
"	$V_{CEX(sus)}$	$I_C = 0.5A, I_{B1} = 0.1A, I_{B2} =$	800			V
"	(1)	$-0.1A, L = 5mH, clamped$				
"	$V_{CEX(sus)}$	$I_C = 0.25A, I_{B1} = 0.05A, I_{B2} =$	900			V
"	(2)	$-0.05A, L = 10mH, clamped$				
Turn-on Time	$t_{on}$	$I_C = 1A, I_{B1} = 0.2A, I_{B2} = -0.4A,$ $R_L = 400ohms, V_{CC} = 400V$			1.0	$\mu s$
Storage Time	$t_{stg}$	" "			3.0	$\mu s$
Fall Time	$t_f$	" "			0.7	$\mu s$

\*: The  $h_{FE}(1)$  of the 2SC3151 is classified as follows. When specifying the  $h_{FE}(1)$  rank, specify two ranks or more in principle.

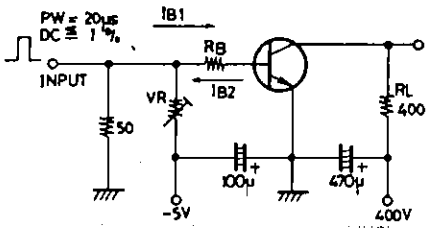
10	K	20	15	L	30	20	M	40
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**Package Dimensions 2022**  
(unit:mm)

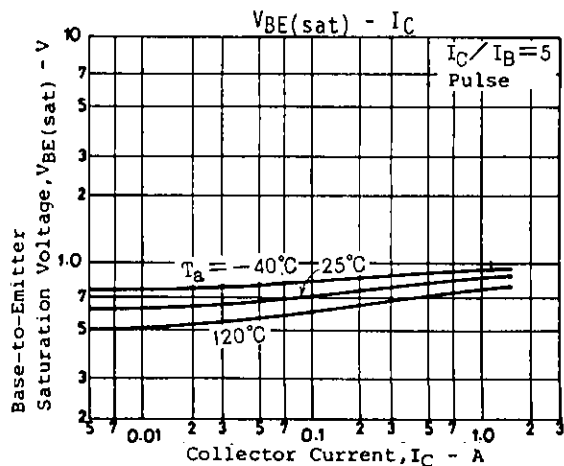
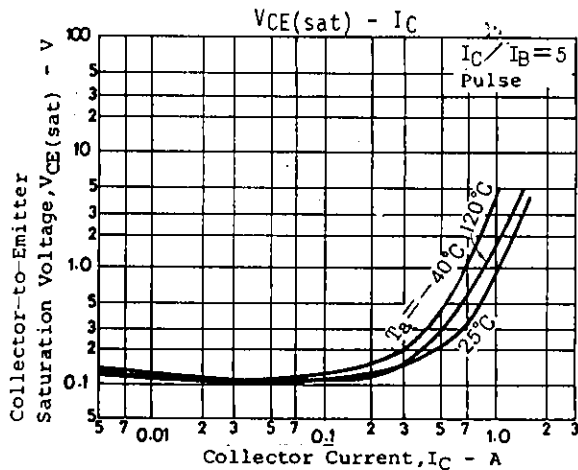
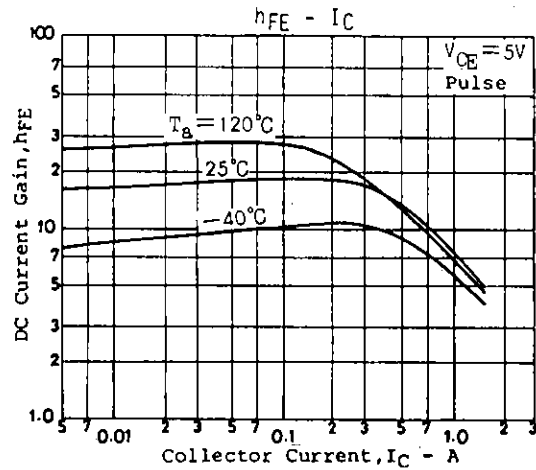
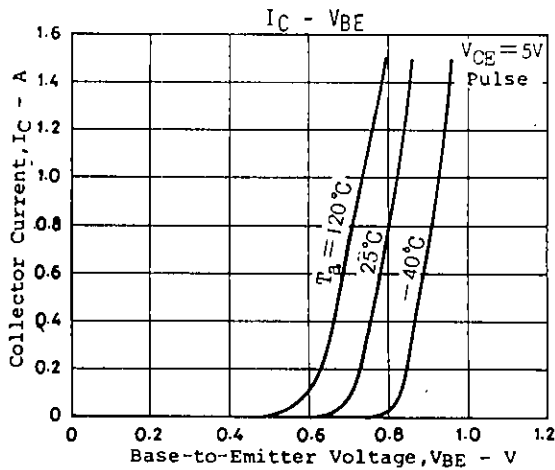
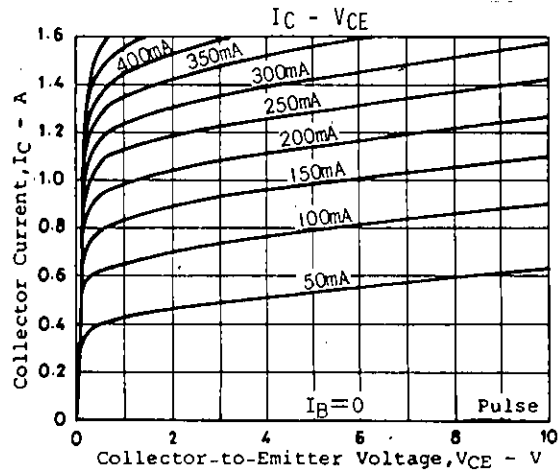
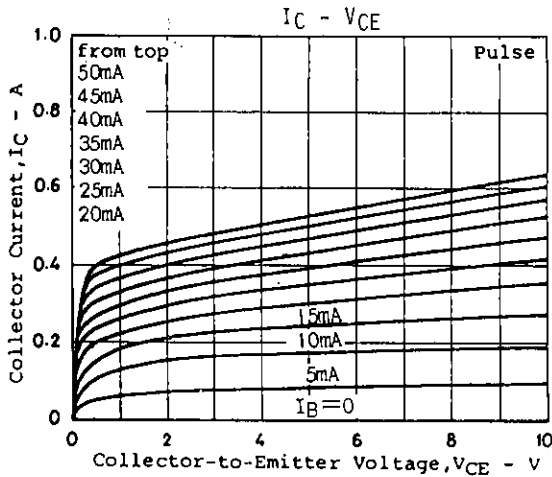


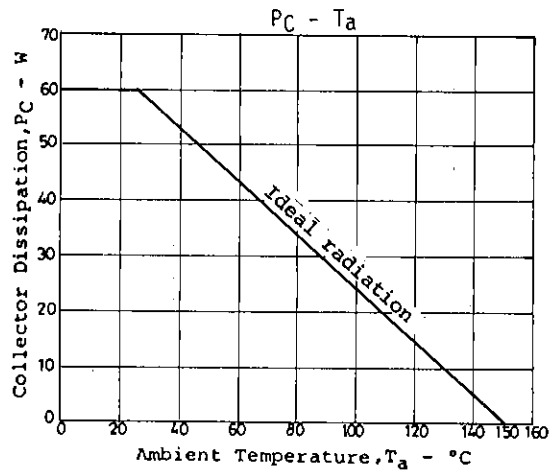
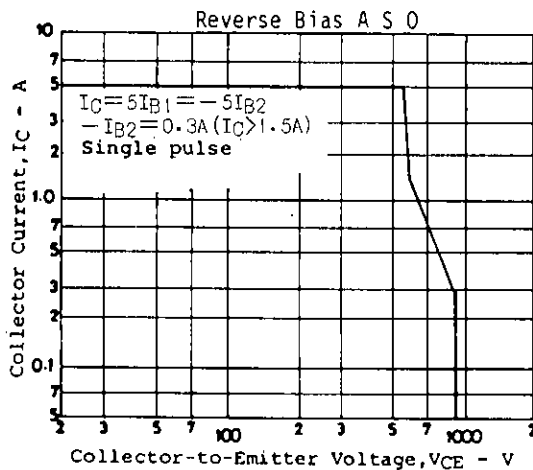
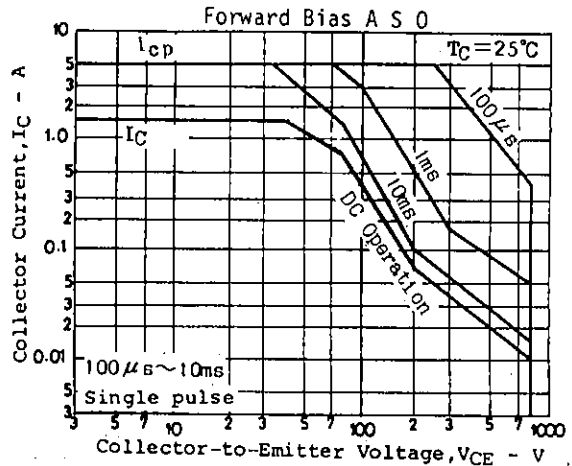
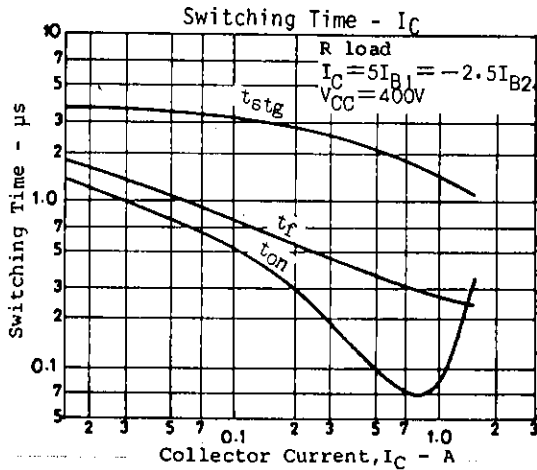
E: Emitter  
C: Collector  
B: Base

Switching Time Test Circuit



Unit (Resistance :  $\Omega$ , Capacitance : F)





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